Amendments to the Claims

- 1. (currently amended) Method A method for the manufacture of a high temperature superconducting layer on a substrate (1a, 1b) comprising the following steps:
 - a. deposition of an RBa₂Cu₃O₇-layer (2) onto the substrate (1a, 1b) with a low growth rate <u>less than 1 nm/s</u>, wherein R represents yttrium, an element of the group of rare-earth elements (atomic number 57-71) or mixtures of two or more of these elements;
 - b. deposition of an XBa₂Cu₃O₇-layer (3) onto the RBa₂Cu₃O₇-layer (2) with a high growth rate <u>greater than 1 nm/s</u>, wherein X represents yttrium, an element of the group of rare-earth elements (atomic number 57-71) or mixtures of two or more of these elements.
- 2. (currently amended) Method A method according to claim 1, wherein the low growth rate is < 1nm/s and wherein the high growth rate is > 1nm/s, preferably > greater than 2 nm/s.
- 3. (currently amended) Method A method according to claim 1 or 2, wherein the RBa₂Cu₃O₇-layer (2) comprises a thickness of [\leq] less than 500 nm, preferably \leq 100 nm.
- 4. (currently amended) Method A method according to claim 1, wherein the $RBa_2Cu_3O_7$ -layer (2) has a thickness of [>] greater than 5 nm.
- 5. (currently amended) Method A method according to claim 1, wherein the $XBa_2Cu_3O_7$ -layer (3) has a thickness of [>] greater than 1 μ m.
- 6. (currently amended) Method A method according to claim 1, wherein the $RBa_2Cu_3O_7$ -layer (2) is deposited onto an at least biaxially textured substrate (1a) or a substrate with an at least biaxially textured buffer layer (1b).

- 7. (currently amended) Method A method according to claim 1, wherein the XBa₂Cu₃O₇-layer (3) is deposited as a precursor layer, comprising the metal components of the high temperature superconducting layer.
- 8. (currently amended) Method A method according to claim 7, wherein the precursor layer is transformed in a further method step by a temperature treatment with a high transformation rate into a superconducting XBa₂Cu₃O₇-layer (3).
- 9. (currently amended) Method A method according to claim 8, wherein the transformation rate is [>] greater than 2 nm/s.
- 10. (currently amended) Method A method according to claim 1, wherein R represents a rare-earth element of the group comprising with a great ion radius (La, Pr, Nd, Sm, Eu, and Gd, [)] or compounds comprising to at least 50% of one or more of these elements in mixtures with other rare-earth elements.
 - 11. (cancelled)